	Ref #	Search Text
74	<b>S74</b>	"LDMOS" (lateral near3 diffus\$3 near5 (transistor gate electode)) "DEMOS" (drain near3 extend\$3 near4 (transistor gate electrode))
75	<b>S75</b>	"CMOS" "PMOS" "NMOS" ("P" near3 (metal adj3 semiconductor)) ("N" near3 (metal adj3 semiconductor))
76	<b>S76</b>	("20020009790" "20020030238" "20020089790" "20030 141559" "20040046226" "20040180485" "20040238913"  "6160289" "6384643" "6400126" "6642697" "6855985"). PN.
77	<b>S77</b>	S74 same S75
78	<b>S78</b>	@ad<= "20031103" or @rlad<= "20031103"
79	<b>S79</b>	S77 and S78
80	S80	("P" near3 body) same ("P" near3 well) ("N" near3 well)
81	S81	("P" near3 body) same (("P" near3 well) ("N" near3 well) well)
82	<b>S82</b>	S81 and S79
83	<b>S83</b>	(438/202).CCLS.
84	S84	(438/204).CCLS.
85	S85	(438/223).CCLS.
86	<b>S86</b>	(438/224).CCLS.
87	S87	(438/227).CCLS.
88	<b>S89</b>	(438/278).CCLS.

	DBs
74	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
75	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
76	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
77	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
78	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
79	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
80	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
81	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
82	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
83	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
84	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
85	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
86	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
87	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
88	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB

	Ref #	Search Text
89	<b>S90</b>	(438/527).CCLS.
90	\$88	(438/275).CCLS.

	DBs
89	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB
90	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB